

In re: Horii Hideki  
Application Serial No.: 10/617,958  
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Page 2

**In the Specification:**

Please replace the paragraph at page 11, lines 25-31 with the following amended paragraph:

As illustrated in Figure 7A, the first and second data storage elements 150a and 151a include first and second phase changeable material patterns 131a and 131[[a]]b, respectively.

The first and second phase changeable material patterns 131a and 131[[a]]b may include a material layer, for example, a Germanium-Antimony-Tellurium (Ge-Sb-Te) layer. It will be understood that the material layer may include tellurium (Te) and/or selenium (Se), which belong to the Chalcogenide family of elements, without departing from the teachings of the present invention.